

IN THE CLAIMS:

Kindly replace claims 7, 12 and 26 as follows:

A₂ 7. (Amended) The method of claim 1, wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

A₃ 12. (Amended) The method of claim 1, wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

A₄ 26. (Amended) The method of claim 1, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

Kindly add new claims 28-40 as follows:

--28. (New) The method of claim 4, wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

A₅ 29. (New) The method of claim 5, wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

30. (New) The method of claim 6, wherein the first buffer layer is formed of multiple semiconductor material layers having different doping concentrations.

31. (New) The method of claim 4, wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

32. (New) The method of claim 5, wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

33. (New) The method of claim 6, wherein the first buffer layer is formed of a semiconductor material layer of a gradient doping concentration that increases upwards.

34. (New) The method of claim 2, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

35. (New) The method of claim 15, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

36. (New) The method of claim 16, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

37. (New) The method of claim 18, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

38. (New) The method of claim 20, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

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cont'd

39. (New) The method of claim 23, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.

40. (New) The method of claim 24, wherein the semiconductor layer is a Group III-V compound semiconductor layer having conductivity.--

P R O C E S S I N G I N F O R M A T I O N